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# Onsemi

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# Very Low Forward Voltage **Trench-based Schottky Rectifier**

# Exceptionally Low $V_F = 0.485$ V at $I_F = 5$ A

#### Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Typical Applications**

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC–DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

#### **Mechanical Characteristics**

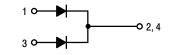
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

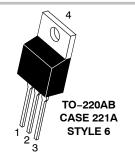


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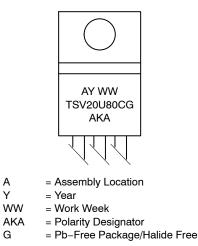
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#### **PIN CONNECTIONS**





#### **MARKING DIAGRAM**



А

Υ

G

WW

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

#### **MAXIMUM RATINGS**

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	80	V
Average Rectified Forward Current (Rated $V_R$ , $T_C$ = 115°C)	Per device Per diode	I <sub>F(AV)</sub>	20 10	A
Peak Repetitive Forward Current (Rated V <sub>R</sub> , Square Wave, 20 kHz, T <sub>C</sub> = 110°C)	Per device Per diode	I <sub>FRM</sub>	40 20	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I <sub>FSM</sub>	100	A
Operating Junction Temperature		TJ	-40 to +150	°C
Storage Temperature		T <sub>stg</sub>	-40 to +150	°C
Voltage Rate of Change (Rated V <sub>R</sub> )		dv/dt	10,000	V/µs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Maximum Thermal Resistance Junction-to-Case	${\sf R}_{ heta {\sf JC}} \ {\sf R}_{ heta {\sf JA}}$	2.0	°C/W
Junction-to-Ambient		70	°C/W

#### ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

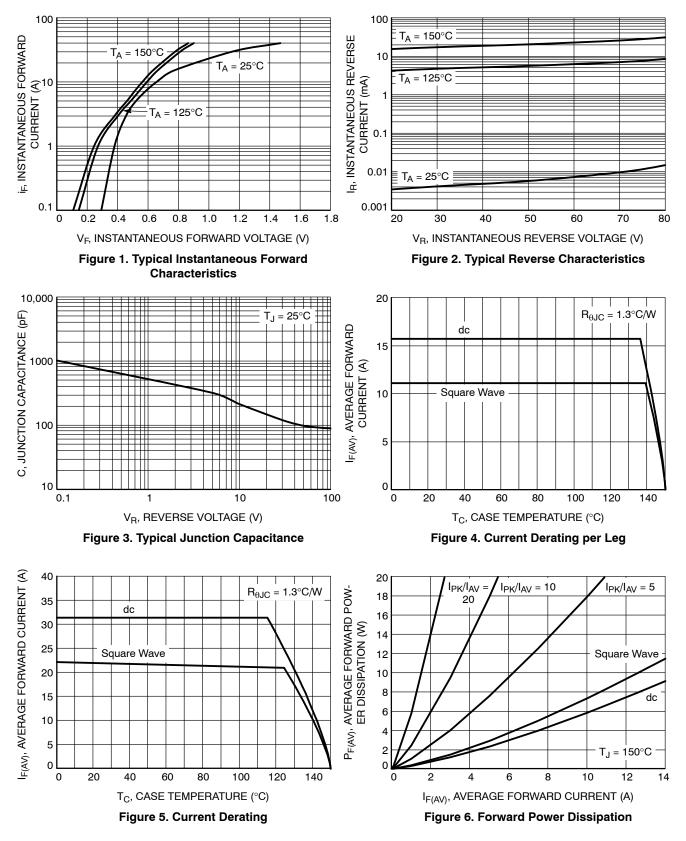
Rating	Symbol	Тур	Max	Unit
	v <sub>F</sub>	0.520 0.658 0.485 0.593	_ 0.98 _ 0.82	V
Maximum Instantaneous Reverse Current (Note 1) (Rated dc Voltage, T <sub>J</sub> = 25°C) (Rated dc Voltage, T <sub>J</sub> = 125°C)	Ι <sub>R</sub>	23 12	600 23	μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width =  $300 \ \mu$ s, Duty Cycle  $\le 2.0\%$ 

#### **ORDERING INFORMATION**

Device	Package	Shipping
NTSV20U80CTG	TO-220AB (Pb-Free/Halide Free)	50 Units / Rail

#### **TYPICAL CHARACTERISTICS**



#### **TYPICAL CHARACTERISTICS**

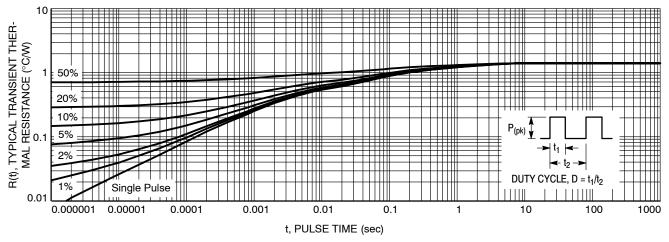
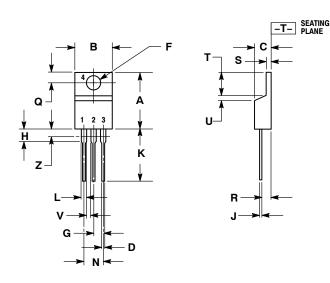


Figure 7. Typical Transient Thermal Response

#### PACKAGE DIMENSIONS

TO-220 CASE 221A-09 ISSUE AH



	INC	HES	MILLIN	ILLIMETERS	
DIM	MIN	MAX	MIN MAX		
Α	0.570	0.620	14.48	15.75	
В	0.380	0.415	9.66	10.53	
С	0.160	0.190	4.07	4.83	
D	0.025	0.038	0.64	0.96	
F	0.142	0.161	3.61	4.09	
G	0.095	0.105	2.42	2.66	
Η	0.110	0.161	2.80	4.10	
J	0.014	0.024	0.36	0.61	
Κ	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
Ν	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Ζ		0.080		2.04	
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DIMENSION Z DEFINES A ZONE WHERE ALL

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#### LITERATURE FULFILLMENT:

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